

PJT7800

20V N-Channel Enhancement Mode MOSFET – ESD Protected

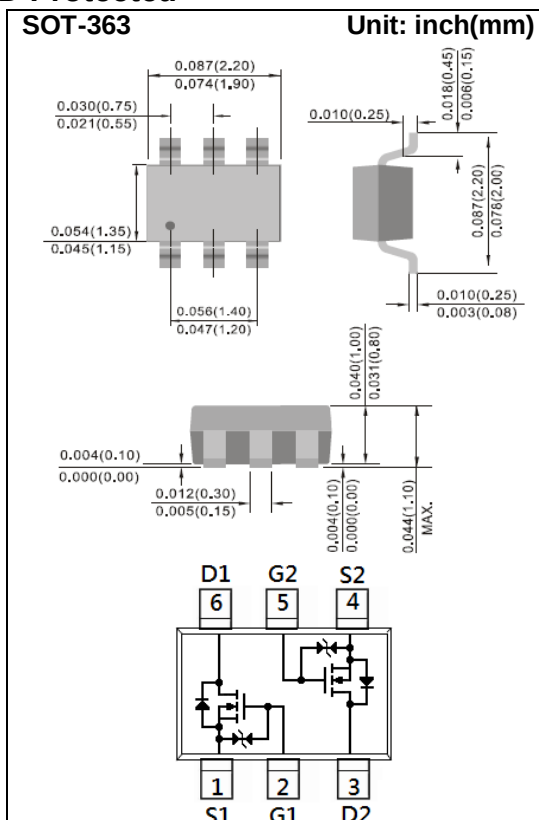
Voltage	20 V	Current	1A
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Features

- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@1.0A < 150m\Omega$
- $R_{DS(ON)}$, $V_{GS}@2.5V$, $I_D@0.7A < 215m\Omega$
- $R_{DS(ON)}$, $V_{GS}@1.8V$, $I_D@0.3A < 400m\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std.(Halogen Free)

Mechanical Data

- Case : SOT-363 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0002 ounces, 0.006 grams
- Marking : T00



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	20	V
Gate-Source Voltage		V _{GS}	±8	V
Continuous Drain Current		I _D	1	A
Pulsed Drain Current (Note 4)		I _{DM}	4	A
Power Dissipation	T _a =25°C	P _D	350	mW
	Derate above 25°C		2.8	mW/°C
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55~150	°C
Typical Thermal resistance		R _{θJA}	357	°C/W
- Junction to Ambient (Note 3)				



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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	20	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.5	0.8	1.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =1A	-	120	150	mΩ
		V _{GS} =2.5V, I _D =0.7A	-	160	215	
		V _{GS} =1.8V, I _D =0.3A	-	260	400	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	-	0.01	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V	-	±2	±10	uA
Dynamic ^(Note 5)						
Total Gate Charge	Q _g	V _{DS} =10V, I _D =1A, V _{GS} =4.5V ^(Note 1,2)	-	1.6	-	nC
Gate-Source Charge	Q _{gs}		-	0.31	-	
Gate-Drain Charge	Q _{gd}		-	0.41	-	
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1.0MHZ	-	92	-	pF
Output Capacitance	C _{oss}		-	25	-	
Reverse Transfer Capacitance	C _{rss}		-	9.1	-	
Turn-On Delay Time	td _(on)	V _{DD} =10V, I _D =1A, V _{GS} =4.5V, R _G =6Ω ^(Note 1,2)	-	5.8	-	ns
Turn-On Rise Time	tr		-	25.8	-	
Turn-Off Delay Time	td _(off)		-	42	-	
Turn-Off Fall Time	tf		-	32	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	1	A
Diode Forward Voltage	V _{SD}	I _S =1.0A, V _{GS} =0V	-	0.85	1.2	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
4. The maximum current rating is package limited
5. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

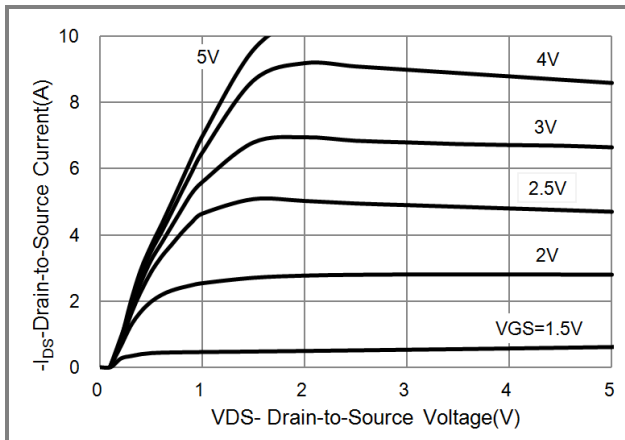


Fig.1 On-Region Characteristics

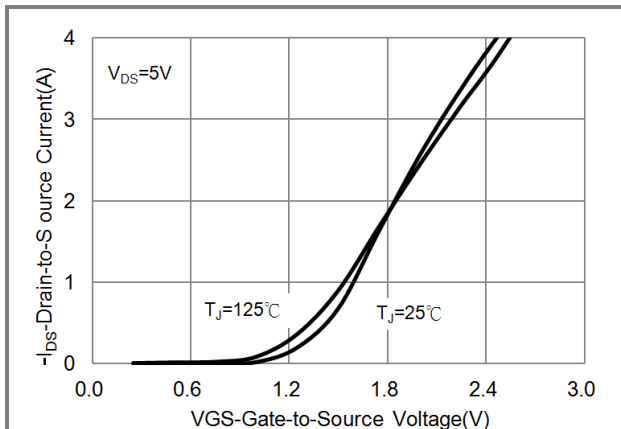


Fig.2 Transfer Characteristics

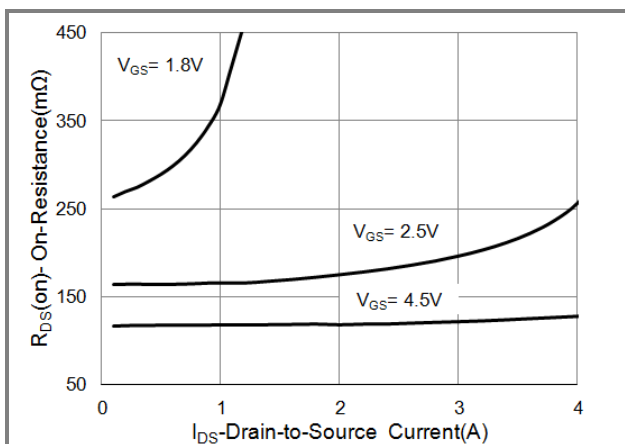


Fig.3 On-Resistance vs. Drain Current

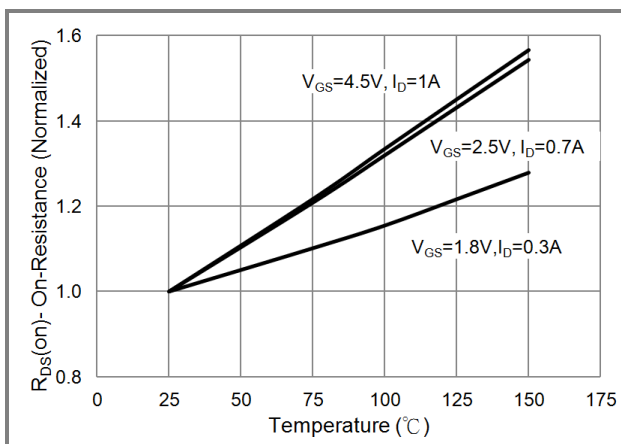


Fig.4 On-Resistance vs. Junction temperature

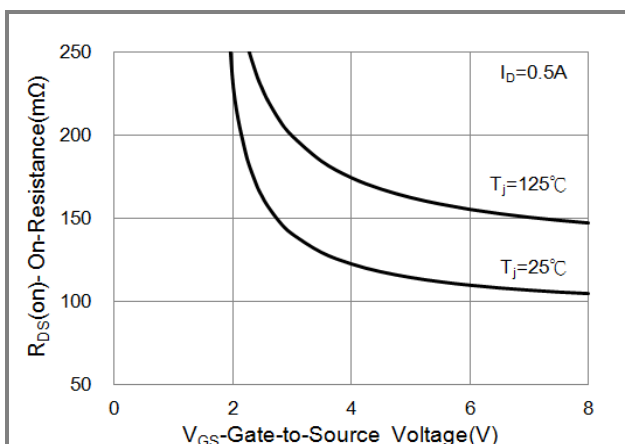


Fig.5 On-Resistance Variation with VGS.

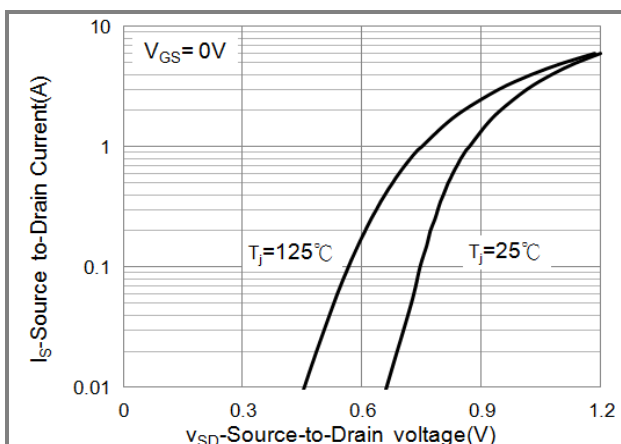


Fig.6 Body Diode Characteristics



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TYPICAL CHARACTERISTIC CURVES

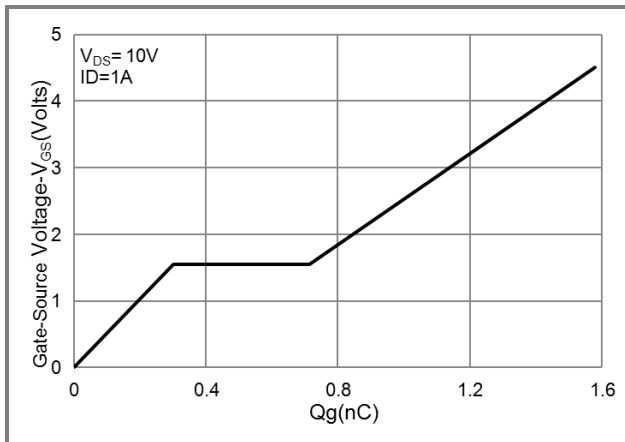


Fig.7 Gate-Charge Characteristics

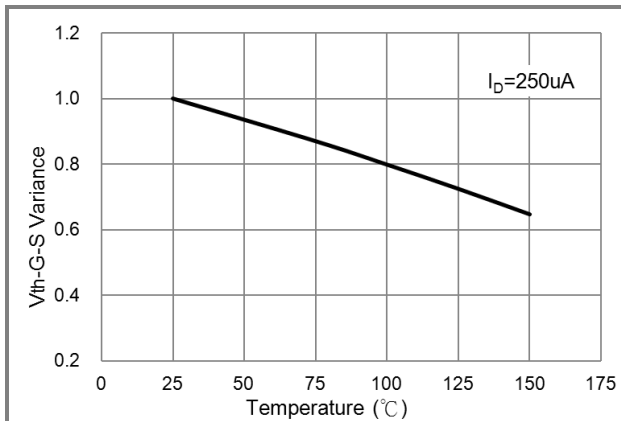


Fig.8 Threshold Voltage Variation with Temperature.

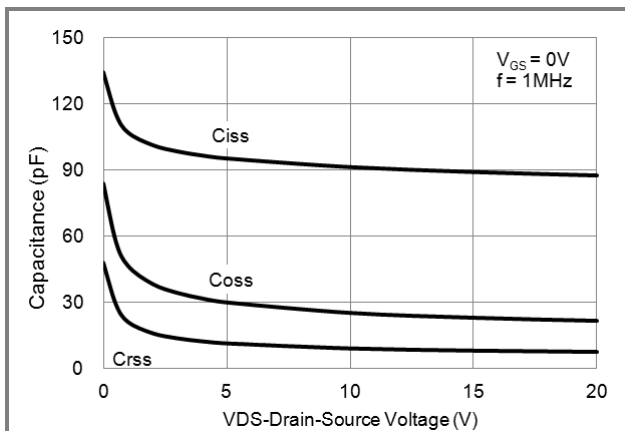


Fig.9 Capacitance vs. Drain-Source Voltage.

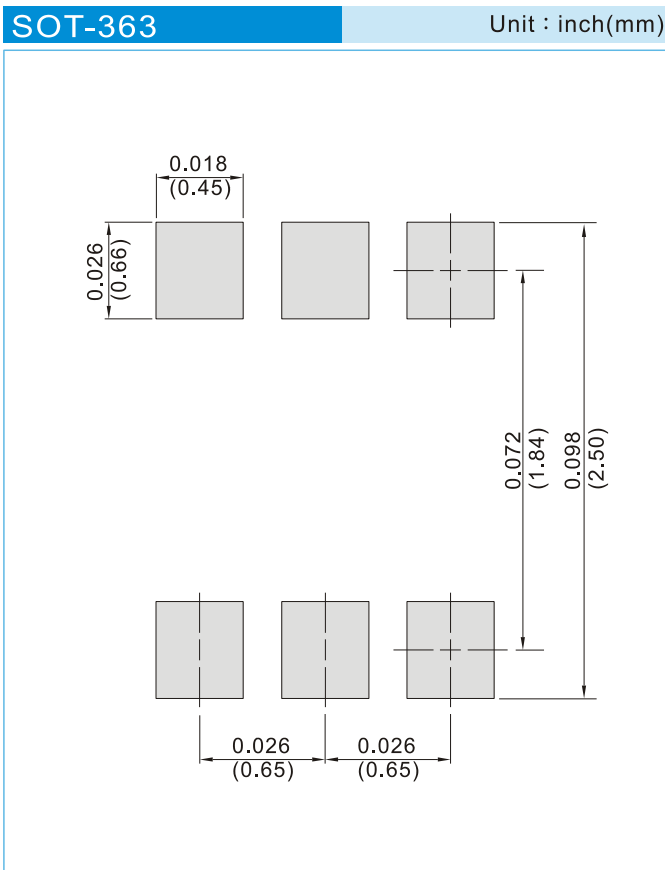


PJT7800

PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJT7800_R1_00001	SOT-363	3K pcs / 7" reel	T00	Halogen free
PJT7800_R2_00001	SOT-363	10K pcs / 13" reel	T00	Halogen free

MOUNTING PAD LAYOUT





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